TENTATIVE

TOSHIBA PHOTOCOUPLER GaAlAs IRED & PHOTO-IC

TLP250F

TRANSISTOR INVERTER

INVERTER FOR AIR CONDITIONOR

IGBT GATE DRIVE

POWER MOS FET GATE DRIVE

The Toshiba TLP250F consists of a GaAlAs light emitting diode and a integrated photodetector.

This unit is 8-lead DIP.

TLP250F is suitable for gate driving circuit of IGBT or power MOS FET.

Input Threshold Current: IF=5mA (Max.)

Supply Current : 11mA (Max.)

Supply Voltage : 10~35V

Output Current $: \pm 1.5A \text{ (Max.)}$

Switching Time : t_{pHL} , $t_{pLH} = 0.5 \mu s$ (Max.)

Isolation Voltage : 2500V_{rms} (Min.)

UL Recognized : UL1577, File No.E67349

Option (D4) type

: DIN VDE0884/06.92、認定No.76823 VDE Approved

Maximum Operating Insulation Voltage: 1140VpK Highest Permissible Over Voltage : 6000 VpK

(Note 1) When a VDE0884 approved type is needed, please designate the "Option (D4)"

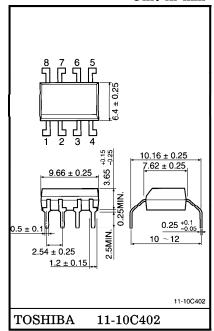
Structural Parameter

: 8.0mm (Min.) Creepage Distance Clearance : 8.0mm (Min.)

TRUTH TABLE

		Tr1	Tr2
Input LED	ON	ON	OFF
	OFF	OFF	ON

Unit in mm



Weight: 0.54g

961001EBC2

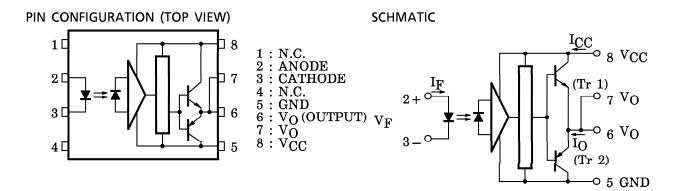
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Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.

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(Note 2) A $0.1\mu\mathrm{F}$ bypass capcitor must be connected between pin 8 and 5.